What is claimed is:

1. A semiconductor device comprising:

an active pattern which includes a lower pattern that extends in a first direction, and a plurality of sheet patterns spaced apart from the lower pattern in a second direction that is perpendicular to the first direction;

a plurality of gate structures which are on the lower pattern and spaced apart from each other in the first direction, each gate structure including a gate electrode and a gate insulating film; and

a source/drain pattern which is between a pair of the gate structures that are adjacent to each other in the first direction, the source/drain pattern including a semiconductor liner film, a semiconductor insertion film on the semiconductor liner film, and a semiconductor filling film on the semiconductor insertion film,

wherein the semiconductor liner film, the semiconductor insertion film, and the semiconductor filling film include silicon-germanium,

wherein a germanium fraction of the semiconductor liner film that is in contact with the plurality of sheet patterns is smaller than a germanium fraction of the semiconductor insertion film and a germanium fraction of the semiconductor filling film,

wherein the semiconductor liner film includes an outer surface that is in contact with the plurality of sheet patterns, and an inner surface that faces the semiconductor filling film,

wherein a liner recess defined by the inner surface of the semiconductor liner film includes a plurality of width extension regions, and

wherein a width of each width extension region in the first direction increases and then decreases as a distance increases in the second direction from an upper surface of the lower pattern.

2. The semiconductor device of claim 1, wherein the inner surface of the semiconductor liner film includes a plurality of convex curved regions and a plurality of concave curved regions.

3. The semiconductor device of claim 1 or claim 2, wherein a first of the width extension regions is between a lower sheet pattern and an upper sheet pattern in the second direction, and wherein a point on which first width extension region has a maximum width in the first direction is located between the lower sheet pattern and the upper sheet pattern.

4. The semiconductor device of any one of claims 1 to 3, wherein the semiconductor insertion film is formed along the inner surface of the semiconductor liner film,

wherein the semiconductor insertion film includes silicon germanium, and

wherein the germanium fraction of the semiconductor insertion film is between the germanium fraction of the semiconductor liner film and the germanium fraction of the semiconductor filling film.

5. The semiconductor device of claim 4, wherein a width of the semiconductor filling film in the first direction increases as a distance increases in the second direction from the lower pattern.

6. The semiconductor device of claim 4 or claim 5, wherein the semiconductor insertion film includes an outer surface that faces the inner surface of the semiconductor liner film, and an inner surface that faces the semiconductor filling film, and

wherein the inner surface of the semiconductor insertion film includes a plurality of convex curved regions and a plurality of concave curved regions.

7. The semiconductor device of claim 1, wherein the semiconductor insertion film further includes a plurality of semiconductor insertion films spaced apart from each other in the second direction,

wherein each of the semiconductor insertion films is between the semiconductor liner film and the semiconductor filling film,

wherein each semiconductor insertion film includes silicon germanium, and

wherein a germanium fraction of each semiconductor insertion film is greater than the germanium fraction of the semiconductor liner film and smaller than the germanium fraction of the semiconductor filling film.

8. The semiconductor device of claim 7, wherein the semiconductor filling film is in contact with the semiconductor liner film.

9. The semiconductor device of claim 7 or claim 8, wherein the inner surface of the semiconductor liner film includes a plurality of convex curved regions and a plurality of concave curved regions, and

wherein at least part of one of the semiconductor insertion films is in one of the concave curved regions.

10. The semiconductor device of any one of claims 1 to 3, wherein an entirety of the inner surface of the semiconductor liner film is in contact with the semiconductor filling film.

11. The semiconductor device of any one of claims 1 to 10, wherein the outer surface of the semiconductor liner film includes a plurality of convex curved regions and a plurality of concave curved regions,

wherein one of the concave curved regions is in contact with a corresponding one of the sheet patterns, and

wherein one of the convex curved regions is in contact with one of the gate insulating films of one of the gate structures.

12. The semiconductor device of claim 1, wherein the outer surface of the semiconductor liner film includes a plurality of planar regions and a plurality of concave curved regions,

wherein one of the concave curved regions is in contact with a corresponding one of the sheet patterns, and

wherein one of the planar regions is in contact with one of the gate insulating films of one of the gate structures.

13. The semiconductor device of claim 1, wherein the outer surface of the semiconductor liner film includes a plurality of first concave curved regions and a plurality of second concave curved regions,

wherein one of the first concave curved regions is in contact with one of the sheet patterns, and

wherein one of the second concave curved regions is in contact with one of the gate insulating films of one of the gate structures.

14. A semiconductor device comprising:

an active pattern which includes a lower pattern that extends in a first direction, and a plurality of sheet patterns spaced apart from the lower pattern in a second direction that is perpendicular to the first direction;

a plurality of gate structures which are on the lower pattern and spaced apart from each other in the first direction, each gate structure including a gate electrode and a gate insulating film; and

a source/drain pattern which is between a pair of the gate structures that are adjacent to each other in the first direction, the source/drain pattern including a semiconductor liner film, a semiconductor insertion film on the semiconductor liner film, and a semiconductor filling film on the semiconductor insertion film,

wherein the semiconductor liner film, the semiconductor insertion film and the semiconductor filling film include silicon-germanium,

wherein a germanium fraction of the semiconductor liner film that is in contact with the plurality of sheet patterns is less than a germanium fraction of the semiconductor insertion film and a germanium fraction of the semiconductor filling film,

wherein the germanium fraction of the semiconductor insertion film is less than the germanium fraction of the semiconductor filling film,

wherein the semiconductor insertion film includes an inner surface that is in contact with the semiconductor filling film, and an outer surface that faces the plurality of sheet patterns,

wherein the outer surface of the semiconductor insertion film includes a plurality of first convex curved regions and a plurality of first concave curved regions, and

wherein the outer surface of the semiconductor insertion film is not in contact with the plurality of sheet patterns.

15. The semiconductor device of claim 14, wherein the inner surface of the semiconductor insertion film includes a plurality of second convex curved regions and a plurality of second concave curved regions.

16. The semiconductor device of claim 14 or claim 15, wherein a width of the semiconductor filling film in the first direction increases as a distance increases in the second direction from the lower pattern.

17. The semiconductor device of any one of claims 14 to 16, wherein the semiconductor liner film surrounds the outer surface of the semiconductor insertion film and is in contact with the semiconductor insertion film, and

wherein the semiconductor liner film is in contact with the plurality of sheet patterns and the lower pattern.

18. A semiconductor device comprising:

an active pattern which includes a lower pattern that extends in a first direction, and a plurality of sheet patterns spaced apart from the lower pattern in a second direction perpendicular to the first direction;

a plurality of gate structures which are on the lower pattern and spaced apart in the first direction, each gate structure including a gate electrode and a gate insulating film; and

a source/drain pattern which is between a pair of the gate structures that are adjacent to each other in the first direction,

wherein each gate structure includes inner gate structure between the lower pattern and the sheet pattern in the second direction, and between each pair of the sheet patterns adjacent to each other in the second direction, each inner gate structure including the gate electrode and the gate insulating film,

wherein the source/drain pattern includes a semiconductor liner film, a semiconductor filling film on the semiconductor liner film, and a semiconductor insertion film between the semiconductor liner film and the semiconductor filling film,

wherein the semiconductor liner film, the semiconductor insertion film and the semiconductor filling film include silicon-germanium,

wherein a germanium fraction of the semiconductor liner film that is in contact with the sheet pattern is less than a germanium fraction of the semiconductor insertion film and a germanium fraction of the semiconductor filling film,

wherein the germanium fraction of the semiconductor insertion film is greater than the germanium fraction of the semiconductor liner film and less than the germanium fraction of the semiconductor filling film,

wherein the semiconductor liner film includes an outer surface which is in contact with the sheet pattern and the inner gate structure, and an inner surface which is in contact with the semiconductor insertion film, and

wherein the inner surface of the semiconductor liner film includes a plurality of convex curved regions and a plurality of concave curved regions.

19. The semiconductor device of claim 18, wherein the semiconductor insertion film includes a plurality of sub-semiconductor insertion films spaced apart in the second direction.

20. The semiconductor device of claim 18, wherein the semiconductor insertion film conforms to the inner surface of the semiconductor liner film.